ELSEVIER

Journal of Crystal Growth 188 (1998) 392–396

JOURNAL OF CRYSTAL GROWTH

Author index

Abernathy, C.R., see Schoenfeld, W. 188 (1998) 50
Abernathy, C.R., see Antonell, M.J. 188 (1998) 113
Abstreiter, G., see Nutsch, A. 188 (1998) 275
Aguilar, L., see Vilela, M.F. 188 (1998) 311
Ahe, M.v.d., see Ungermanns, Ch. 188 (1998) 32
Aiba, Y., see Hashimoto, A. 188 (1998) 75
Aigle, M., see Limmer, W. 188 (1998) 225
Albrecht, P., see Künzel, H. 188 (1998) 281
Alexandre, F., see Jahan, D. 188 (1998) 176
Antonell, M.J., see Schoenfeld, W. 188 (1998) 50
Antonell, M.J., C.R. Abernathy, A. Sher, M. Berding, M. Van Schilfgaarde, A. Sanjuro and K. Wong, Growth of Tl-containing III–V materials by gas-source molecular beam epitaxy 188 (1998) 113
Aoyagi, Y., see Shen, X.Q. 188 (1998) 86
Aoyagi, Y., see Ozasa, K. 188 (1998) 370
Asahi, H., see Iwata, K. 188 (1998) 98
Asahi, H., see Koh, H. 188 (1998) 107
Asahi, H., see Sato, J. 188 (1998) 363
Asami, K., see Iwata, K. 188 (1998) 98
Asami, K., see Koh, H. 188 (1998) 107
Asami, K., see Sato, J. 188 (1998) 363
Asbeck, P.M., see Hsin, Y.M. 188 (1998) 355
Avanci, L.H., M.A. Hayashi, L.P. Cardoso, S.L. Morelhão, F. Riesz, K. Rakennus and T. Hakkarainen, Mapping of Bragg-surface diffraction of InP/GaAs(1 0 0) structure 188 (1998) 220

Baumeister, H., see Keidler, M. 188 (1998) 168
Baumeister, H., see Popp, M. 188 (1998) 247
Baumeister, H., E. Veuhoff, M. Popp and H. Heinecke, GRINSCH GaInAsP MQW laser structures grown by MOMBE 188 (1998) 266
Behrend, J., J.F. Carlin, A.V. Sirbu, C.A. Berseth, A. Rudra and E. Kapon, InAsP/InGaAsP periodic gain structure for 1.5μm vertical cavity surface emitting laser applications 188 (1998) 295
Behrend, J., see Rudra, A. 188 (1998) 300
Behrend, J., see Syrbu, A.V. 188 (1998) 338
Benchimol, J.L., see Jahan, D. 188 (1998) 176
Benchimol, J.L., J. Mba, A.M. Duchenois, B. Sermage, P. Launay, D. Caffin, M. Meghelli and M. Juhel, CBE growth of carbon doped InGaAs/InP HBTs for 25 Gbit/s circuits 188 (1998) 349
Berding, M., see Antonell, M.J. 188 (1998) 113
Berseth, C.A., see Behrend, J. 188 (1998) 295
Berseth, C.A., see Rudra, A. 188 (1998) 300
Berseth, C.A., see Syrbu, A.V. 188 (1998) 338
Bitzer, K., see Schneider, J.M. 188 (1998) 56
Brown, N., see Pearsall, T.P. 188 (1998) 63
Bullough, T.J., see Hill, D. 188 (1998) 21

Cacciatore, C., see Rigo, C. 188 (1998) 317
Caffin, D., see Benchimol, J.L. 188 (1998) 349
Campi, D., see Rigo, C. 188 (1998) 317
Cardoso, L.P., see Avanci, L.H. 188 (1998) 220
Carius, R., see Ungermanns, Ch. 188 (1998) 32
Carlin, J.F., see Behrend, J. 188 (1998) 295
Carlin, J.F., see Rudra, A. 188 (1998) 300
Carlin, J.F., see Syrbu, A.V. 188 (1998) 338
Chen, M.-C., M.C.H. Liao and H.-H. Lin, Self-organized InAs/GaAs quantum dots grown on (1 0 0) misoriented substrates by molecular beam epitaxy 188 (1998) 383
Cohen, G.M. and D. Ritter, Room temperature operation of $Ga_xIn_{1-x}P/Ga_{0.47}In_{0.53}As$ resonant tunneling diodes 188 (1998) 359
Coriasso, C., see Rigo, C. 188 (1998) 317
Cui, J., M. Ozeki and M. Ohashi, Dynamical approach to the surface reaction of triisobutylgallium (TIBGa) on GaAs(0 0 1) by using molecular beam scattering 188 (1998) 137

Dahlheimer, B., see Nutsch, A. 188 (1998) 275
Davidson, B.R., see Joyce, T.B. 188 (1998) 211
Davies, G.J., see Foord, J.S. 188 (1998) 144
Davies, G.J., see Foord, J.S. 188 (1998) 159
Dehaese, O., see Rudra, A. 188 (1998) 300
Deller, H.R., see Rosenblad, C. 188 (1998) 125
Döhr, N., see Nutsch, A. 188 (1998) 275
Druminski, M., see Keidler, M. 188 (1998) 168
Duchenois, A.M., see Benchimol, J.L. 188 (1998) 349

0022-0248/98/$19.00 © 1998 Elsevier Science B.V. All rights reserved.
PII S0022-0248(98)00453-9

Ebert, S., see Künzel, H. 188 (1998) 281
Egorov, A.Yu., A.R. Kovsh, V.M. Ustinov, A.E. Zhukoh, P.S. Kop'ev and C.W. Tu, A thermodynamic analysis of the growth of III–V compounds with two volatile group V elements by molecular-beam epitaxy 188 (1998) 69

Farrell, T., see Hill, D. 188 (1998) 21
Farrell, T., see Jothilingam, R. 188 (1998) 39
Farrell, T., see Joyce, T.B. 188 (1998) 211
Faustini, L., see Rigo, C. 188 (1998) 317
Fernandez, J., see Syrbu, A.V. 188 (1998) 338
Foord, J.S., F.P. Howard, G.S. McGrady and G.J. Davies, Reactivity patterns of stibine and trisdimethylaminoantimony precursors for chemical beam epitaxial growth and etching 188 (1998) 144
Foord, J.S., F.P. Howard and G.J. Davies, Reaction models for the homoepitaxial and selected area growth of GaSb by MOMBE 188 (1998) 159
Förster, A., see Ungermanns, Ch. 188 (1998) 32
Freundlich, A., see Vilela, M.F. 188 (1998) 311
Freundlich, A., see Monier, C. 188 (1998) 332
Fujita, K., H. Watanabe and M. Ichikawa, Nanoscale Si selective homoepitaxial growth observed by scanning tunneling microscopy 188 (1998) 197
Fushida, M., see Koh, H. 188 (1998) 107

Garcia, J.Ch., Potential and prospects of CBE technology compared to MBE as production tool for microwave devices 188 (1998) 343
Gastaldi, L., see Rigo, C. 188 (1998) 317
Gerster, J., see Limmer, W. 188 (1998) 225
Giannakopoulos, K.P. and P.J. Goodhew, Striation development in CBE-grown vicinal plane InGaAs layers 188 (1998) 26
Gibis, R., see Künzel, H. 188 (1998) 281
Gonda, S., see Iwata, K. 188 (1998) 98
Gonda, S., see Koh, H. 188 (1998) 107
Gonda, S., see Sato, J. 188 (1998) 363
Goodhew, P.J., see Giannakopoulos, K.P. 188 (1998) 26
Goodhew, P.J., see Jothilingam, R. 188 (1998) 39
Graf, T., see Rosenblad, C. 188 (1998) 125

Hakkarainen, T., see Avanci, L.H. 188 (1998) 220
Harde, P., see Künzel, H. 188 (1998) 281
Hardtdegen, H., see Ungermanns, Ch. 188 (1998) 32
Harmsma, P.J., see Verschuren, C.A. 188 (1998) 288
Hasegawa, F., see Yonemura, S. 188 (1998) 81
Hashimoto, A., Y. Aiba, Y. Kurumi and A. Yamamoto, Nitridation of $In_xGa_{1-x}As$ by dimethyl-hydrazine (DMHy) 188 (1998) 75
Hatanaka, A., see Yoshimoto, M. 188 (1998) 92
Hatatani, S., K. Yuasa and M. Konagai, MOMBE growth of InGaP on (1 0 0) and (4 1 1)A GaAs substrates using tertiarybutylphosphine (TBP) 188 (1998) 17
Hayashi, M.A., see Avanci, L.H. 188 (1998) 220
Heinecke, H., see Schneider, J.M. 188 (1998) 56
Heinecke, H., see Ritter, D. 188 (1998) 152
Heinecke, H., see Keidler, M. 188 (1998) 168
Heinecke, H., see Marheineke, B. 188 (1998) 183
Heinecke, H., see Limmer, W. 188 (1998) 225
Heinecke, H., see Popp, M. 188 (1998) 247
Heinecke, H., see Baumeister, H. 188 (1998) 266
Hidaka, K., see Sato, J. 188 (1998) 363
Hill, D., T. Farrell, T.B. Joyce and T.J. Bullough, A comparison of the transitory periods in GaAs and AlGaAs CBE growth 188 (1998) 21
Homma, Y., see Tanahashi, K. 188 (1998) 205
Howard, F.P., see Foord, J.S. 188 (1998) 144
Howard, F.P., see Foord, J.S. 188 (1998) 159
Hsin, Y.M., N.Y. Li, C.W. Tu and P.M. Asbeck, AlGaAs/GaAs HBTs with extrinsic base regrowth 188 (1998) 355

Iakovlev, V.P., see Syrbu, A.V. 188 (1998) 338
Ichikawa, M., see Fujita, K. 188 (1998) 197
Ikeda, H., see Okada, M. 188 (1998) 119
Inoue, H., see Kondow, M. 188 (1998) 255
Inoue, N., see Tanahashi, K. 188 (1998) 205
Inoue, N., see Kawamura, Y. 188 (1998) 307
Inoue, N., see Yoshimatsu, K. 188 (1998) 328
Itoh, H., see Yoshimoto, M. 188 (1998) 92
Itoh, M., see Sugiura, H. 188 (1998) 260
Iwai, S., see Shen, X.Q. 188 (1998) 86
Iwamura, H., see Kawamura, Y. 188 (1998) 307
Iwata, K., H. Asahi, K. Asami, R. Kuroiwa and S. Gonda, Strong photoluminescence emission from GaN grown on amorphous silica substrates by gas source MBE 188 (1998) 98
Izena, A., M. Sakuraba, T. Matsuura and J. Murota, Low-temperature reaction of CH_4 on Si(1 0 0) 188 (1998) 131

Jahan, D., F. Alexandre and J.L. Benchimol, Beam geometrical modelling of CBE on nonplanar substrate 188 (1998) 176
Johnson, M., see Pearsall, T.P. 188 (1998) 63
Jothilingam, R., T. Farrell, T.B. Joyce and P.J. Goodhew, Low-temperature laser assisted CBE-growth of AlGaAs 188 (1998) 39
Joyce, T.B., see Hill, D. 188 (1998) 21
Joyce, T.B., see Jothilingam, R. 188 (1998) 39
Joyce, T.B., T. Farrell and B.R. Davidson, Reflectance anisotropy spectroscopy studies of the growth of carbon-doped GaAs by chemical beam epitaxy 188 (1998) 211
Juhel, M., see Benchimol, J.L. 188 (1998) 349

Kaiser, R., see Künzel, H. 188 (1998) 281
Kamada, A., see Kawamura, Y. 188 (1998) 307
Kamada, A., see Yoshimatsu, K. 188 (1998) 328
Kapon, E., see Behrend, J. 188 (1998) 295
Kapon, E., see Rudra, A. 188 (1998) 300
Kapon, E., see Syrbu, A.V. 188 (1998) 338
Kawamura, Y., see Tanahashi, K. 188 (1998) 205
Kawamura, Y., K. Yoshimatsu, A. Kamada, H. Iwamura and N. Inoue, Structural dependence of optical bistability of $In_{0.52}Al_{0.48}As/InP$ type II MQW diodes grown by gas source molecular beam epitaxy 188 (1998) 307
Kawamura, Y., see Yoshimatsu, K. 188 (1998) 328
Keidler, M., see Ritter, D. 188 (1998) 152
Keidler, M., D. Ritter, H. Baumeister, M. Druminski and H. Heinecke, Planar selective area growth of DH laser structures using hydrides, tertiarybutyl and ditertiarybutyl group V precursors in MOMBE 188 (1998) 168
Kim, S.-B., J.-R. Ro and E.-H. Lee, Vertical stacking of strained InGaAs/GaAs quantum wires by chemical beam epitaxy 188 (1998) 191
Kim, S.-B., see Ro, J.-R. 188 (1998) 377
Kitatani, T., see Kondow, M. 188 (1998) 255
Kizuki, H., see Künzel, H. 188 (1998) 281
Koh, H., H. Asahi, M. Fushida, K. Yamamoto, K. Takenaka, K. Asami, S. Gonda and K. Oe, Photoconductance measurement on TlInGaP grown by gas source MBE 188 (1998) 107
Konagai, M., see Hatatani, S. 188 (1998) 17
Kondo, Y., see Sugiura, H. 188 (1998) 260
Kondow, M., T. Kitatani, M.C. Larson, K. Nakahara, K. Uomi and H. Inoue, Gas-source MBE of GaInNAs for long-wavelength laser diodes 188 (1998) 255
Kop'ev, P.S., see Egorov, A.Yu. 188 (1998) 69
Kovsh, A.R., see Egorov, A.Yu. 188 (1998) 69
Kratzer, H., see Nutsch, A. 188 (1998) 275
Künzel, H., R. Gibis, H. Kizuki, P. Albrecht, S. Ebert, P. Harde, S. Malchow and R. Kaiser, MOMBE grown GaInAsP ($\lambda_g = 1.05/1.15$ μm) waveguide for laser integrated photonic ICs 188 (1998) 281
Kurisu, H., see Yoshimatsu, K. 188 (1998) 328
Kuroiwa, R., see Iwata, K. 188 (1998) 98
Kurumi, Y., see Hashimoto, A. 188 (1998) 75

Larson, M.C., see Kondow, M. 188 (1998) 255
Launay, P., see Benchimol, J.L. 188 (1998) 349
Lee, E.-H., see Kim, S.-B. 188 (1998) 191
Lee, E.-H., see Ro, J.-R. 188 (1998) 377
Leifer, K., see Rudra, A. 188 (1998) 300
Leys, M.R., see Verschuren, C.A. 188 (1998) 11
Leys, M.R., see Verschuren, C.A. 188 (1998) 288
Li, N.Y. and C.W. Tu, Low-resistance polycrystalline GaAs grown by gas-source molecular beam epitaxy using CBr_4 188 (1998) 45
Li, N.Y., see Hsin, Y.M. 188 (1998) 355
Liao, M.C.H., see Chen, M.-C. 188 (1998) 383
Limmer, W., J. Gerster, M. Aigle, J. Porsche, J.M. Schneider, B. Marheineke, H. Heinecke and R. Sauer, Spatially resolved characterization of material composition and free carrier concentration by micro-Raman spectroscopy at surface selectively grown layers 188 (1998) 225
Lin, H.-H., see Chen, M.-C. 188 (1998) 383
Lukas, R., see Nutsch, A. 188 (1998) 275
Lüth, H., see Ungermanns, Ch. 188 (1998) 32

Malchow, S., see Künzel, H. 188 (1998) 281
Marheineke, B., E. Veuhoff and H. Heinecke, Dopant incorporation behaviour during MOMBE growth of InP on (1 0 0), {1 1 1} and nonplanar surfaces 188 (1998) 183
Marheineke, B., see Limmer, W. 188 (1998) 225
Marschner, T., see Verschuren, C.A. 188 (1998) 11
Matsunami, H., see Yoshimoto, M. 188 (1998) 92
Matsuura, T., see Izena, A. 188 (1998) 131
Matt, M., see Ungermanns, Ch. 188 (1998) 32
Mba, J., see Benchimol, J.L. 188 (1998) 349
McGrady, G.S., see Foord, J.S. 188 (1998) 144
Meghelli, M., see Benchimol, J.L. 188 (1998) 349
Miller, M.S., see Ohlsson, B.J. 188 (1998) 387
Mitsuhara, M., see Sugiura, H. 188 (1998) 260
Monier, C., see Vilela, M.F. 188 (1998) 311
Monier, C., M.F. Vilela, I. Serdiukova and A. Freundlich, Photocurrent and photoluminescence spectroscopy of $InAs_xP_{1-x}/InP$ strained quantum wells grown by chemical beam epitaxy 188 (1998) 332
Morelhão, S.L., see Avanci, L.H. 188 (1998) 220
Müller, E., see Rosenblad, C. 188 (1998) 125
Murota, J., see Izena, A. 188 (1998) 131
Muto, A., see Okada, M. 188 (1998) 119

Naito, H., see Yoshimatsu, K. 188 (1998) 328
Nakahara, K., see Kondow, M. 188 (1998) 255
Newman, F., see Vilela, M.F. 188 (1998) 311
Nutsch, A., B. Dahlheimer, N. Döhr, H. Kratzer, R. Lukas, B. Torabi, G. Tränkle, G. Abstreiter and G. Weimann, Chemical beam epitaxy of integrated 1.55 μm lasers on exact and misoriented (1 0 0)-InP substrates 188 (1998) 275

Oe, K., see Koh, H. 188 (1998) 107
Oei, Y.S., see Verschuren, C.A. 188 (1998) 288
Ogasawara, M., see Sugiura, H. 188 (1998) 260
Ohashi, M., see Cui, J. 188 (1998) 137

Ohlsson, B.J. and M.S. Miller, Growth of strained GaAs islands on (0 0 1) GaP: a RHEED study of quantum wire formation 188 (1998) 387
Okada, M., A. Muto, H. Ikeda, S. Zaima and Y. Yasuda, Nucleation and growth of Ge on Si(1 1 1) by MBE with additional atomic hydrogen irradiation studied by scanning tunneling microscopy 188 (1998) 119
Osaka, J., see Tanahashi, K. 188 (1998) 205
Ozasa, K. and Y. Aoyagi, In situ composition control of self-organized InGaAs dots 188 (1998) 370
Ozeki, M., see Cui, J. 188 (1998) 137

Pearsall, T.P., N. Brown, N.L. Ricker and M. Johnson, Flux monitoring and control in epitaxy by chemical vapor deposition 188 (1998) 63
Popp, M., H. Baumeister, E. Veuhoff and H. Heinecke, Element incorporation in GaInAsP for uniform large area MOMBE 188 (1998) 247
Popp, M., see Baumeister, H. 188 (1998) 266
Porsche, J., see Limmer, W. 188 (1998) 225

Rakennus, K., see Avanci, L.H. 188 (1998) 220
Ricker, N.L., see Pearsall, T.P. 188 (1998) 63
Rieger, J., see Schneider, J.M. 188 (1998) 56
Riesz, F., see Avanci, L.H. 188 (1998) 220
Rigo, C., L. Gastaldi, D. Campi, L. Faustini, C. Coriasso, C. Cacciatore and D. Soldani, Multiple quantum well compressive strained heterostructures for low driving power all-optical waveguide switches 188 (1998) 317
Ritter, D., M. Keidler and H. Heinecke, Growth of InP using TBP and DTBP in metalorganic molecular beam epitaxy 188 (1998) 152
Ritter, D., see Keidler, M. 188 (1998) 168
Ritter, D., see Cohen, G.M. 188 (1998) 359
Ro, J.-R., see Kim, S.-B. 188 (1998) 191
Ro, J.-R., S.-B. Kim and E.-H. Lee, Formation of GaAs island by Ga-droplet-induced chemical beam epitaxy 188 (1998) 377
Rosenblad, C., H.R. Deller, T. Graf, E. Müller and H. von Känel, Low temperature epitaxial growth by LEPECVD 188 (1998) 125
Rudra, A., see Behrend, J. 188 (1998) 295
Rudra, A., L. Sagalowicz, K. Leifer, J. Behrend, C.-A. Berseth, O. Dehaese, J.F. Carlin and E. Kapon, Evaluation of InP/InGaAsP distributed Bragg reflectors grown by chemical-beam epitaxy 188 (1998) 300
Rudra, A., see Syrbu, A.V. 188 (1998) 338

Sagalowicz, L., see Rudra, A. 188 (1998) 300
Sakuraba, M., see Izena, A. 188 (1998) 131
Sanjuro, A., see Antonell, M.J. 188 (1998) 113
Sato, J., H. Asahi, T. Tashima, K. Hidaka, K. Yamamoto, K. Asami and S. Gonda, Formation of InAs quantum dots by metalorganic molecular beam epitaxy using trisdimethylaminoarsenic and bisdimethylaminoarsenicchloride 188 (1998) 363
Sauer, R., see Limmer, W. 188 (1998) 225
Schmidt, R., see Ungermanns, Ch. 188 (1998) 32
Schneider, J.M., K. Bitzer, J. Rieger and H. Heinecke, Highly carbon-doped $Ga_{0.47}In_{0.53}As$ contact layers grown by using carbontetrabromide in MBE on MOVPE 1.55 μm GaInAsP/InP MQW laser structures 188 (1998) 56
Schneider, J.M., see Limmer, W. 188 (1998) 225
Schoenfeld, W., M.J. Antonell and C.R. Abernathy, Doping of InSb and InAs using CBr_4 during growth by gas source molecular beam epitaxy 188 (1998) 50
Serdiukova, I., see Monier, C. 188 (1998) 332
Sermage, B., see Benchimol, J.L. 188 (1998) 349
Shen, X.Q., S. Tanaka, S. Iwai and Y. Aoyagi, Chemical beam epitaxy of GaN using triethylgallium and ammonia 188 (1998) 86
Sher, A., see Antonell, M.J. 188 (1998) 113
Shimoyama, N., see Yonemura, S. 188 (1998) 81
Shiraki, Y., see Sugita, T. 188 (1998) 323
Sirbu, A.V., see Behrend, J. 188 (1998) 295
Soldani, D., see Rigo, C. 188 (1998) 317
Suemasu, T., see Yonemura, S. 188 (1998) 81
Suemune, I., see Uesugi, K. 188 (1998) 103
Sugita, T., N. Usami and Y. Shiraki, Enhanced no-phonon transition in indirect GaAsP/GaP quantum wells by insertion of monolayer AlP for electron localization 188 (1998) 323
Sugiura, H., M. Ogasawara, M. Mitsuhara, M. Itoh and Y. Kondo, CBE growth of 2%-strained InAsP MQWs for 1.5 μm wavelength laser diodes 188 (1998) 260
Swartzentruber, B.S., Fundamentals of surface step and island formation mechanisms 188 (1998) 1
Syrbu, A.V., J. Behrend, J. Fernandez, J.F. Carlin, C.-A. Berseth, V.P. Iakovlev, A. Rudra and E. Kapon, Thermal stability of InP-based structures for wafer fused laser diodes 188 (1998) 338

Takenaka, K., see Koh, H. 188 (1998) 107
Tanahashi, K., Y. Kawamura, N. Inoue, Y. Homma and J. Osaka, Surface-roughening processes in GaAs MBE studied by in situ scanning electron microscopy 188 (1998) 205
Tanaka, S., see Shen, X.Q. 188 (1998) 86
Tashima, T., see Sato, J. 188 (1998) 363
Torabi, B., see Nutsch, A. 188 (1998) 275
Tränkle, G., see Nutsch, A. 188 (1998) 275
Tsuchiya, H., see Yonemura, S. 188 (1998) 81
Tu, C.W., see Li, N.Y. 188 (1998) 45
Tu, C.W., see Egorov, A.Yu. 188 (1998) 69

Tu, C.W., see Hsin, Y.M. 188 (1998) 355

Uesugi, K. and I. Suemune, Band gap energy of GaNAs grown on GaAs(0 0 1) substrates by metalorganic molecular-beam epitaxy 188 (1998) 103
Ungermanns, Ch., H. Hardtdegen, M. Matt, A. Förster, M.v.d. Ahe, R. Carius, R. Schmidt and H. Lüth, MOMBE and characterization of InAs and (Al,Ga)Sb 188 (1998) 32
Uomi, K., see Kondow, M. 188 (1998) 255
Usami, N., see Sugita, T. 188 (1998) 323
Ustinov, V.M., see Egorov, A.Yu. 188 (1998) 69

Van Schilfgaarde, M., see Antonell, M.J. 188 (1998) 113
Verschuren, C.A., M.R. Leys, T. Marschner, H. Vonk and J.H. Wolter, A modified BCF model to quantitatively describe the (1 0 0)InP growth rate in chemical beam epitaxy 188 (1998) 11
Verschuren, C.A., P.J. Harmsma, Y.S. Oei, M.R. Leys, H. Vonk and J.H. Wolter, Butt-coupling loss of 0.1 dB/interface in InP/InGaAs MQW waveguide-waveguide structures grown by selective area chemical beam epitaxy 188 (1998) 288
Veuhoff, E., see Marheineke, B. 188 (1998) 183
Veuhoff, E., Potential of MOMBE/CBE for the production of photonic devices in comparison with MOVPE 188 (1998) 231
Veuhoff, E., see Popp, M. 188 (1998) 247
Veuhoff, E., see Baumeister, H. 188 (1998) 266
Vilela, M.F., A. Freundlich, C. Monier, F. Newman and L. Aguilar, Chemical beam epitaxy for high-efficiency InP solar cells 188 (1998) 311
Vilela, M.F., see Monier, C. 188 (1998) 332
Von Känel, H., see Rosenblad, C. 188 (1998) 125
Vonk, H., see Verschuren, C.A. 188 (1998) 11
Vonk, H., see Verschuren, C.A. 188 (1998) 288

Watanabe, H., see Fujita, K. 188 (1998) 197
Weimann, G., see Nutsch, A. 188 (1998) 275
Wolter, J.H., see Verschuren, C.A. 188 (1998) 11
Wolter, J.H., see Verschuren, C.A. 188 (1998) 288
Wong, K., see Antonell, M.J. 188 (1998) 113

Yaguchi, T., see Yonemura, S. 188 (1998) 81
Yamamoto, A., see Hashimoto, A. 188 (1998) 75
Yamamoto, K., see Koh, H. 188 (1998) 107
Yamamoto, K., see Sato, J. 188 (1998) 363
Yasuda, Y., see Okada, M. 188 (1998) 119
Yonemura, S., T. Yaguchi, H. Tsuchiya, N. Shimoyama, T. Suemasu and F. Hasegawa, Comparison between monomethyl hydrazine and ECR plasma activated nitrogen as a nitrogen source for CBE growth of GaN 188 (1998) 81
Yoshimatsu, K., see Kawamura, Y. 188 (1998) 307
Yoshimatsu, K., Y. Kawamura, H. Kurisu, A. Kamada, H. Naito and N. Inoue, Optical and electrical properties of InAlAs/AlAsSb type II quantum well structures grown by molecular beam epitaxy 188 (1998) 328
Yoshimoto, M., A. Hatanaka, H. Itoh and H. Matsunami, GaN growth on sapphire and 6H-SiC by metalorganic molecular beam epitaxy 188 (1998) 92
Yuasa, K., see Hatatani, S. 188 (1998) 17

Zaima, S., see Okada, M. 188 (1998) 119
Zhukov, A.E., see Egorov, A.Yu. 188 (1998) 69

ELSEVIER

Journal of Crystal Growth 188 (1998) 397–398

JOURNAL OF CRYSTAL GROWTH

Subject index

Computer simulation
– of chemical beam epitaxy 176

Device characterization
– diodes 311, 328, 338, 359
– electronic materials 225, 343
– heterojunctions 328, 332, 338, 349
– heterostructures 231
– lasers 56, 168, 231, 255, 260, 288, 338
– photonic integrated circuits 288
– quantum structures 191, 231, 255, 260, 300, 307, 317, 332, 338, 363, 370, 377, 383, 387
– solar cells 311
– surface selectively grown layers 225
– wave guides 281
Diffusional control
– of doping profile 266
Diodes, see Device characterization
Doping of
– carbon in indium gallium arsenide 56, 349
– carbon in indium gallium phosphide 17
– nitrogen in indium gallium arsenide 75
– silicon in indium phosphide 183
– zinc in indium phosphide 183

Electronic materials, see Device characterization
Epitaxy, see Thin films
Etching
– chemical 144, 338
– photolithographic 311, 338

Heterojunctions, see Device characterization
Heterostructures, see Device characterization

Kinetics
– of diffusion 1
– of growth 1, 11, 17, 21, 56, 119, 159, 168, 205, 247
– of interface control 75, 205, 260, 332
– of nitridation 75
– of nucleation 11, 119, 205
– of step flow 11
– of surface reaction 137
– of tertiarybutylphosphine pyrolysis 152

Lasers, see Device characterization
Lasers, crystals for
– high carbon doping 56
– photonic integrated circuits 281

Morphological stability
– of self-organized dots 370

Precursor, for
– gallium arsenide 45, 137
– gallium indium arsenide phosphide 168
– gallium nitride 81, 86
– indium gallium arsenide 75
– indium phosphide 152

Quantum structures, see Device characterization

Solar cells, see Device characterization
Superlattices, multilayers of
– indium phosphide/indium gallium arsenide 288
Surface structure of
– gallium antimonide 159
– gallium arsenide 211
– germanium films on silicon surfaces 119
– indium gallium arsenide 26
– selectively grown laser structures 168

Thin film growth, epitaxy
– by chemical beam epitaxy
– – of gallium antimonide 144
– – of gallium arsenide 191
– – of indium antimonide 144
– – of indium gallium arsenide 191, 349, 370
– – of indium gallium arsenide phosphide 370
– – of indium phosphide 338
– – of silicon 197
– by metalorganic molecular beam epitaxy
– – of aluminum antimonide 32
– – of aluminum gallium antimonide 32
– – of aluminum gallium arsenide 21, 39, 355
– – of aluminum phosphide 323
– – of gallium antimonide 32, 159
– – of gallium arsenide 21, 45, 211, 343, 355, 377, 387
– – of gallium arsenide phosphide 323

0022-0248/98/$19.00 © 1998 Elsevier Science B.V. All rights reserved.
PII S0022-0248(98)00454-0

– – of gallium nitride 81, 86, 92, 98
– – of gallium nitride arsenide 103
– – of indium aluminum arsenide 307, 317
– – of indium antimonide 50
– – of indium arsenide 32, 50, 363
– – of indium arsenide phosphide 260, 332
– – of indium gallium arsenide 26, 75, 225, 317, 359
– – of indium gallium arsenide phosphide 168, 231, 247, 260, 266, 275, 281, 295, 300
– – of indium gallium phosphide 17, 295, 343, 359
– – of indium phosphide 11, 152, 176, 183, 231, 260, 300, 307, 311, 317, 332
– – theory of surface diffusion 11
– by molecular beam epitaxy
– – of aluminum arsenide antimonide 328
– – of gallium arsenide 205, 220, 343, 383
– – of gallium indium arsenide 56
– – of gallium indium nitride arsenide 255
– – of gallium indium phosphide 343
– – of germanium 119
– – of indium aluminum arsenide 328
– – of indium arsenide 383
– – of indium phosphide 220
– – of indium thallium antimonide 113
– – of indium thallium arsenide 113
– – of indium thallium phosphide 113
– – of silicon 1
– – of thallium antimonide 113
– – of thallium arsenide 113
– – of thallium indium gallium phosphide 107
– – of thallium phosphate 113
– – thermodynamic theory of growth 69
– by selective area chemical beam epitaxy
– – of indium gallium arsenide 288
– – of indium phosphide 288
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of carbon 131
– – – of general flux in situ monitoring 63
– – – of plasma enhanced silicon germanium growth 125
– – through metalorganic chemical vapor deposition
– – – of gallium indium arsenide 56
– – – of indium gallium arsenide phosphide 275
– – – of indium phosphide 231